

# STARPOWER

SEMICONDUCTOR

**IGBT**

## GD100FFT120C6S\_T4

**1200V/100A 6 in one-package**

### General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as general inverters and UPS.

### Features

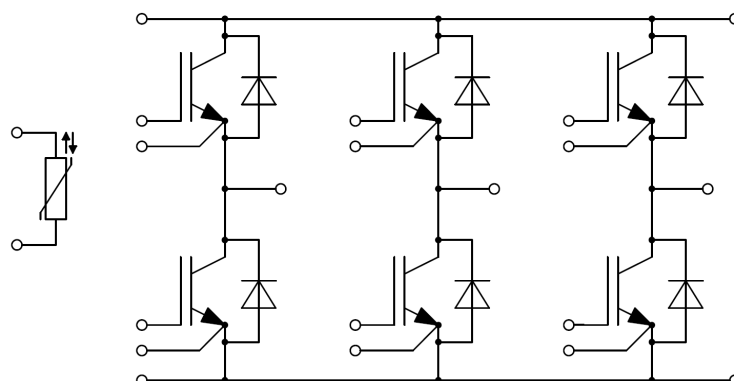
- Low  $V_{CE(sat)}$  Trench IGBT technology
- 10 $\mu$ s short circuit capability
- $V_{CE(sat)}$  with positive temperature coefficient
- Maximum junction temperature 175°C
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology



### Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

### Equivalent Circuit Schematic



**Absolute Maximum Ratings**  $T_C=25^{\circ}\text{C}$  unless otherwise noted**IGBT**

Symbol	Description	Value	Unit
$V_{CES}$	Collector-Emitter Voltage	1200	V
$V_{GES}$	Gate-Emitter Voltage	$\pm 20$	V
$I_C$	Collector Current @ $T_C=25^{\circ}\text{C}$	150	A
	@ $T_C=100^{\circ}\text{C}$	100	
$I_{CM}$	Pulsed Collector Current $t_p=1\text{ms}$	200	A
$P_D$	Maximum Power Dissipation @ $T_j=175^{\circ}\text{C}$	547	W

**Diode**

Symbol	Description	Value	Unit
$V_{RRM}$	Repetitive Peak Reverse Voltage	1200	V
$I_F$	Diode Continuous Forward Current	100	A
$I_{FM}$	Diode Maximum Forward Current $t_p=1\text{ms}$	200	A

**Module**

Symbol	Description	Value	Unit
$T_{jmax}$	Maximum Junction Temperature	175	$^{\circ}\text{C}$
$T_{jop}$	Operating Junction Temperature	-40 to +150	$^{\circ}\text{C}$
$T_{STG}$	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
$V_{ISO}$	Isolation Voltage RMS, $f=50\text{Hz}, t=1\text{min}$	4000	V

**IGBT Characteristics**  $T_c=25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=100\text{A}, V_{GE}=15\text{V}, T_j=25^\circ\text{C}$		1.75	2.20	V	
		$I_C=100\text{A}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}$		2.05			
		$I_C=100\text{A}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}$		2.10			
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=3.8\text{mA}, V_{CE}=V_{GE}, T_j=25^\circ\text{C}$	5.1	5.8	6.4	V	
$I_{CES}$	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$			1.0	mA	
$I_{GES}$	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^\circ\text{C}$			100	nA	
$R_{Gint}$	Internal Gate Resistance			7.5		$\Omega$	
$C_{ies}$	Input Capacitance	$V_{CE}=25\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		6.30		nF	
$C_{res}$	Reverse Transfer Capacitance			0.27		nF	
$Q_G$	Gate Charge	$V_{GE}=-15\dots+15\text{V}$		0.80		$\mu\text{C}$	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=100\text{A}, R_G=4.7\Omega, V_{GE}=\pm 15\text{V}, T_j=25^\circ\text{C}$		279		ns	
$t_r$	Rise Time			64		ns	
$t_{d(off)}$	Turn-Off Delay Time			305		ns	
$t_f$	Fall Time			188		ns	
$E_{on}$	Turn-On Switching Loss			5.65		mJ	
$E_{off}$	Turn-Off Switching Loss			6.10		mJ	
$t_{d(on)}$	Turn-On Delay Time		$V_{CC}=600\text{V}, I_C=100\text{A}, R_G=4.7\Omega, V_{GE}=\pm 15\text{V}, T_j=125^\circ\text{C}$		286		ns
$t_r$	Rise Time				68		ns
$t_{d(off)}$	Turn-Off Delay Time			339		ns	
$t_f$	Fall Time			284		ns	
$E_{on}$	Turn-On Switching Loss			7.85		mJ	
$E_{off}$	Turn-Off Switching Loss			10.0		mJ	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=100\text{A}, R_G=4.7\Omega, V_{GE}=\pm 15\text{V}, T_j=150^\circ\text{C}$			292		ns
$t_r$	Rise Time				69		ns
$t_{d(off)}$	Turn-Off Delay Time			352		ns	
$t_f$	Fall Time			322		ns	
$E_{on}$	Turn-On Switching Loss			8.64		mJ	
$E_{off}$	Turn-Off Switching Loss			11.0		mJ	
$I_{SC}$	SC Data		$t_p \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}, V_{CC}=900\text{V}, V_{CEM} \leq 1200\text{V}$		360		A

**Diode Characteristics**  $T_c=25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_F$	Diode Forward Voltage	$I_F=100\text{A}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$		1.70	2.15	V
		$I_F=100\text{A}, V_{GE}=0\text{V}, T_j=125^\circ\text{C}$		1.65		
		$I_F=100\text{A}, V_{GE}=0\text{V}, T_j=150^\circ\text{C}$		1.65		
$Q_r$	Recovered Charge			8.0		$\mu\text{C}$
$I_{RM}$	Peak Reverse Recovery Current	$V_R=600\text{V}, I_F=100\text{A},$ $-di/dt=1650\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=25^\circ\text{C}$		78		A
$E_{rec}$	Reverse Recovery Energy			3.83		mJ
$Q_r$	Recovered Charge			14.3		$\mu\text{C}$
$I_{RM}$	Peak Reverse Recovery Current	$V_R=600\text{V}, I_F=100\text{A},$ $-di/dt=1650\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=125^\circ\text{C}$		102		A
$E_{rec}$	Reverse Recovery Energy			6.94		mJ
$Q_r$	Recovered Charge			16.5		$\mu\text{C}$
$I_{RM}$	Peak Reverse Recovery Current	$V_R=600\text{V}, I_F=100\text{A},$ $-di/dt=1650\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=150^\circ\text{C}$		113		A
$E_{rec}$	Reverse Recovery Energy			8.05		mJ

**NTC Characteristics**  $T_c=25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$R_{25}$	Rated Resistance			5.0		$\text{k}\Omega$
$\Delta R/R$	Deviation of $R_{100}$	$T_c=100^\circ\text{C}, R_{100}=493.3\Omega$	-5		5	%
$P_{25}$	Power Dissipation				20.0	mW
$B_{25/50}$	B-value	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15\text{K}))]$		3375		K

**Module Characteristics**  $T_c=25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
$L_{CE}$	Stray Inductance		21		nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal to Chip		1.80		$\text{m}\Omega$
$R_{\theta JC}$	Junction-to-Case (per IGBT)			0.274	K/W
	Junction-to-Case (per Diode)			0.468	
$R_{\theta CS}$	Case-to-Sink (per IGBT)		0.086		K/W
	Case-to-Sink (per Diode)		0.146		
$R_{\theta CS}$	Case-to-Sink		0.009		K/W
M	Mounting Torque, Screw M6	3.0		6.0	N.m
G	Weight of Module		300		g

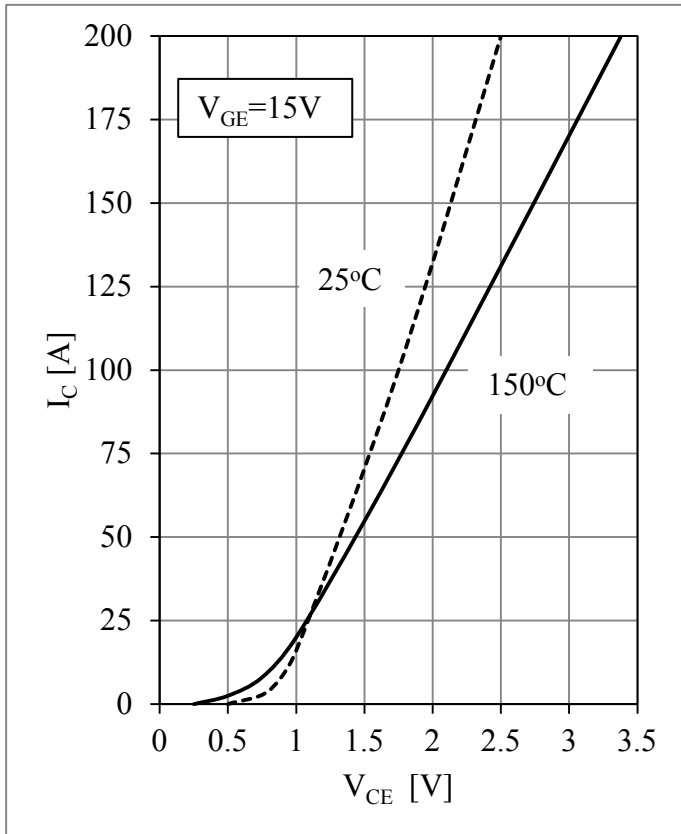


Fig 1. IGBT Output Characteristics

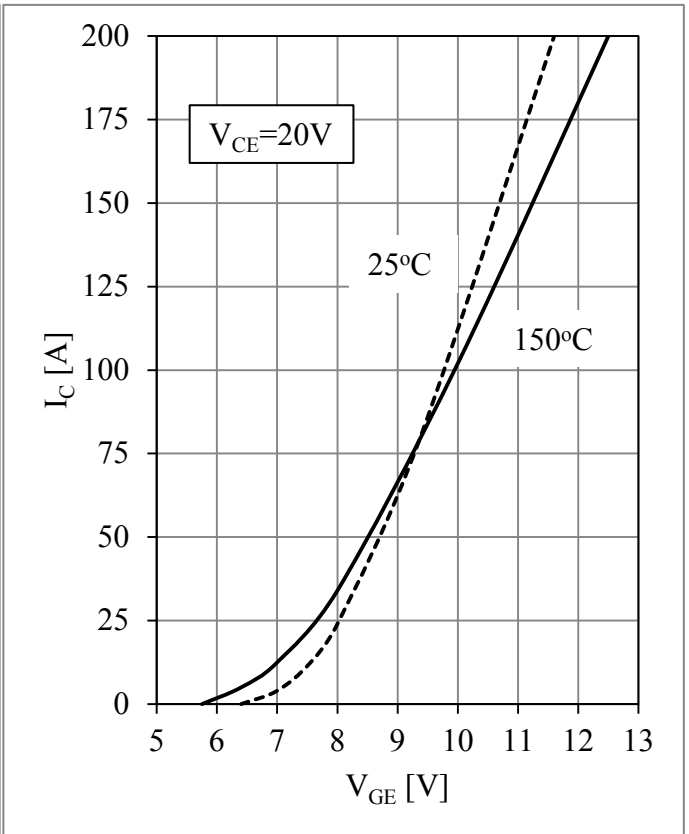


Fig 2. IGBT Transfer Characteristics

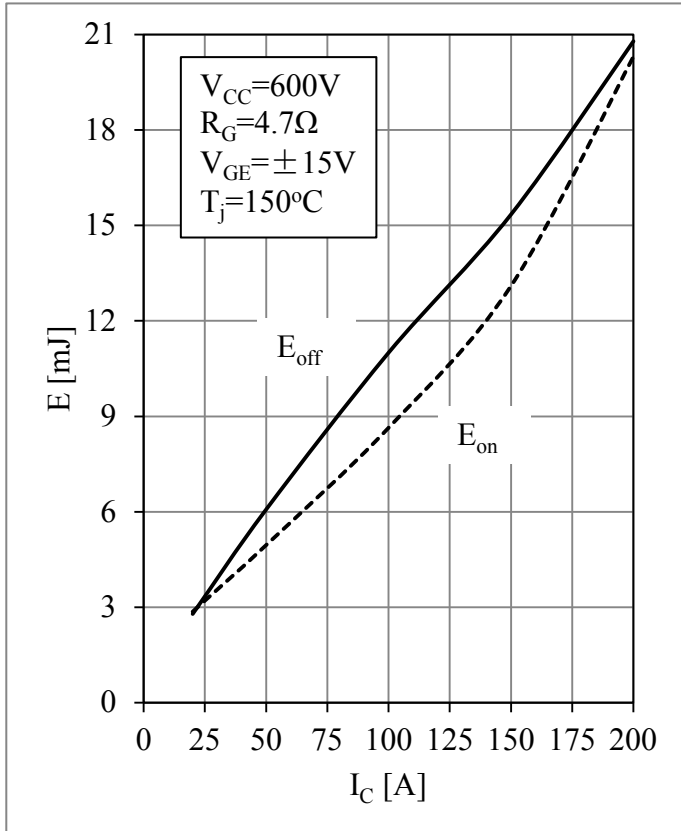


Fig 3. IGBT Switching Loss vs.  $I_c$

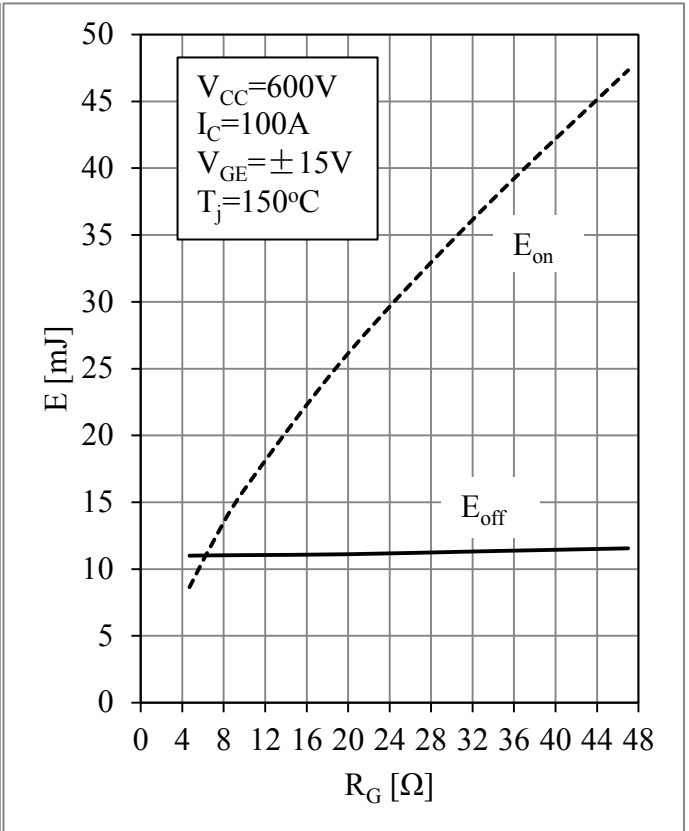


Fig 4. IGBT Switching Loss vs.  $R_G$

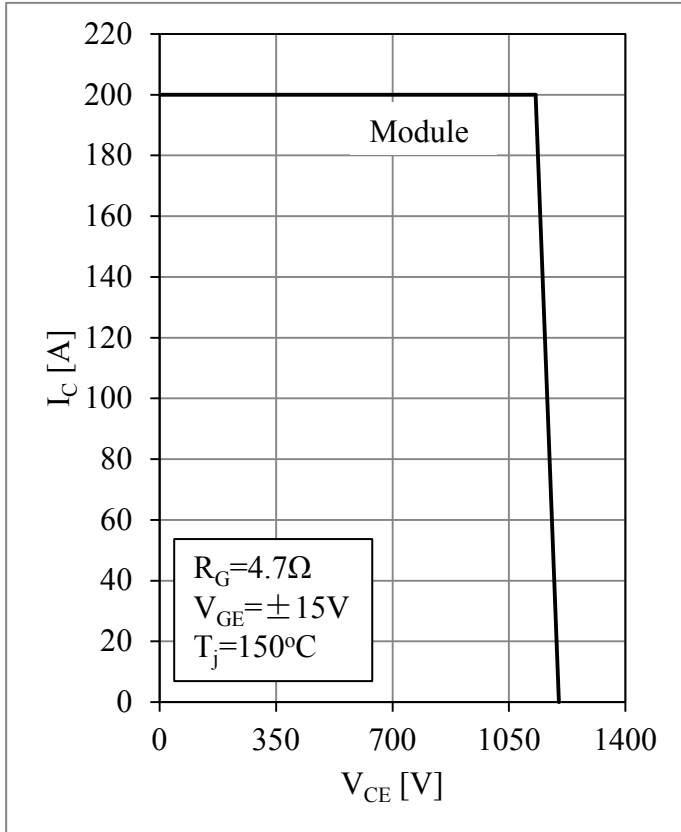


Fig 5. RBSOA

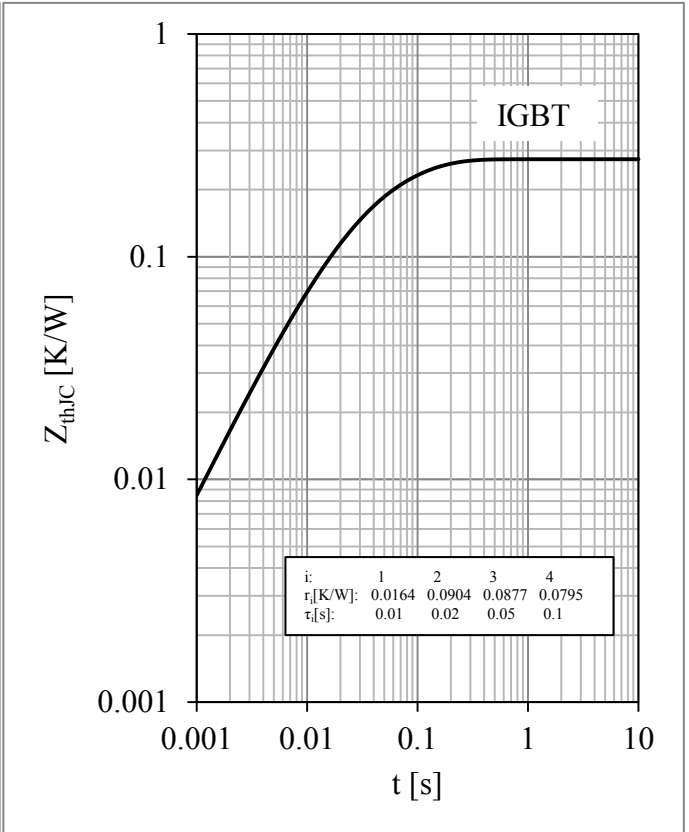


Fig 6. IGBT Transient Thermal Impedance

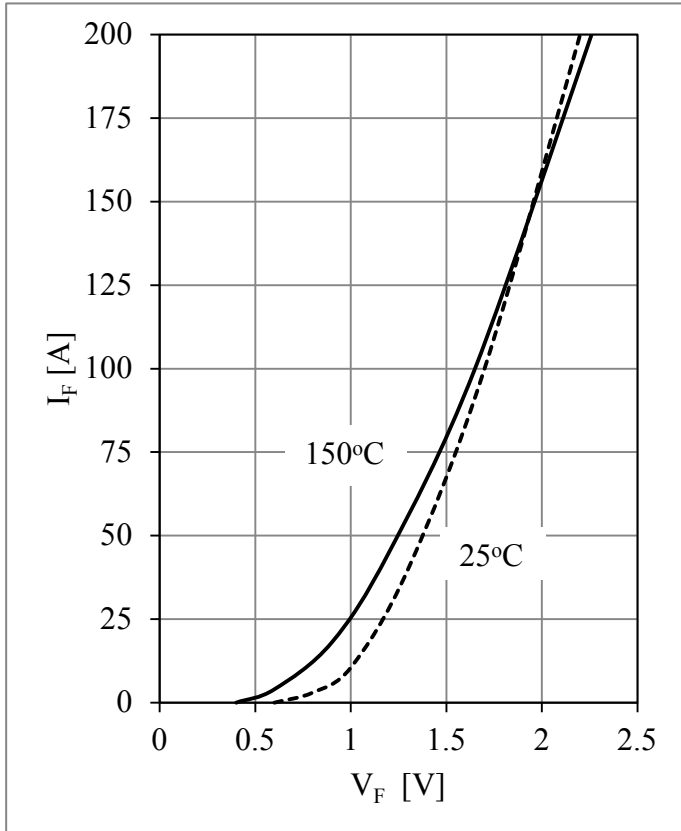


Fig 7. Diode Forward Characteristics

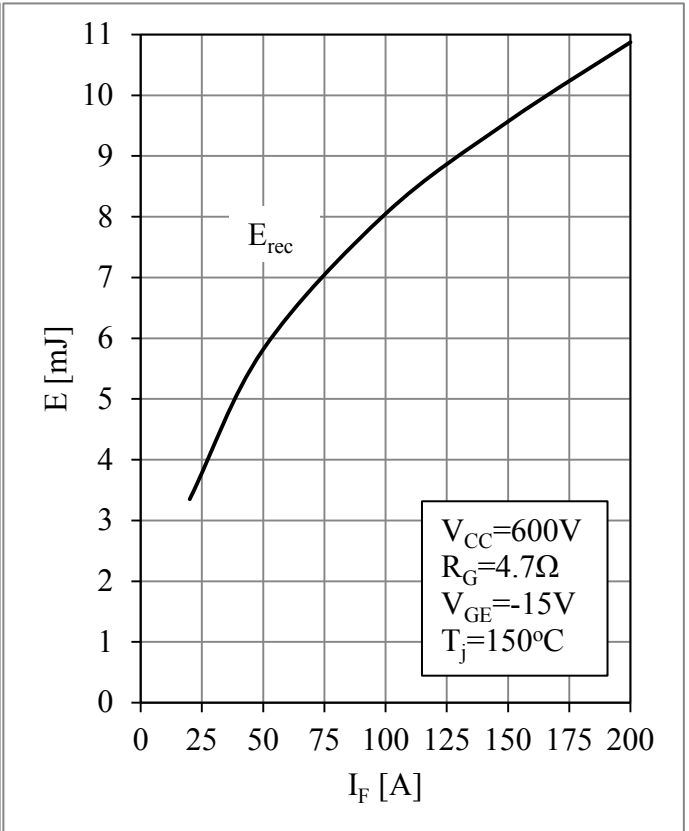


Fig 8. Diode Switching Loss vs.  $I_F$

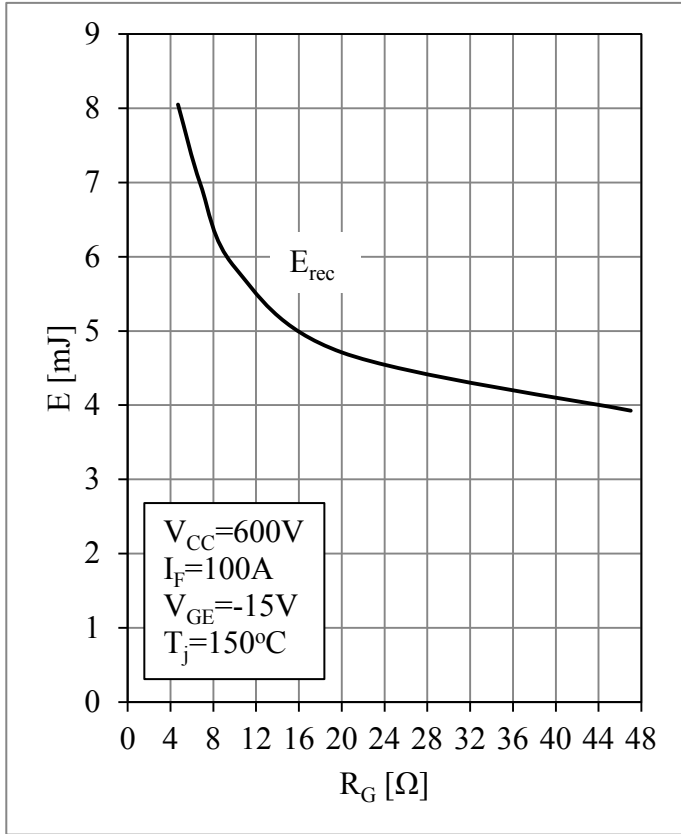


Fig 9. Diode Switching Loss vs.  $R_G$

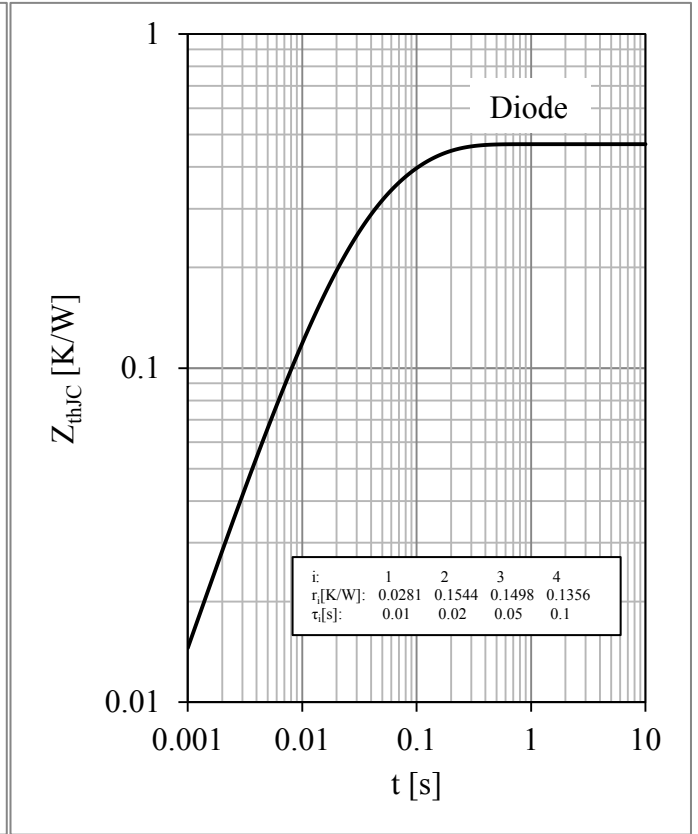


Fig 10. Diode Transient Thermal Impedance

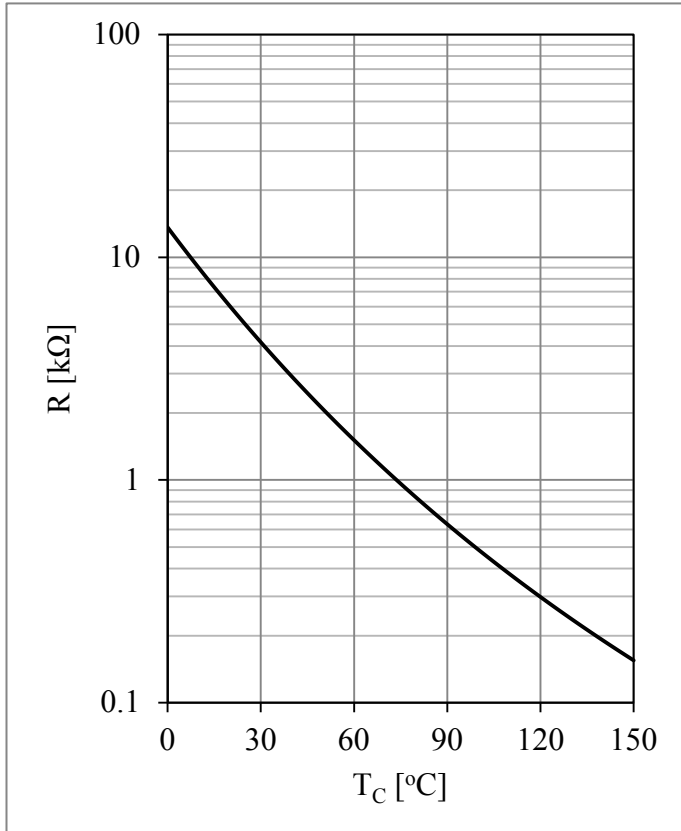
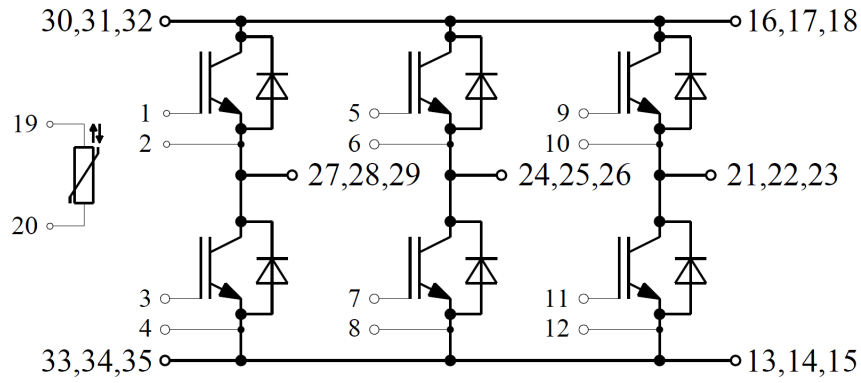


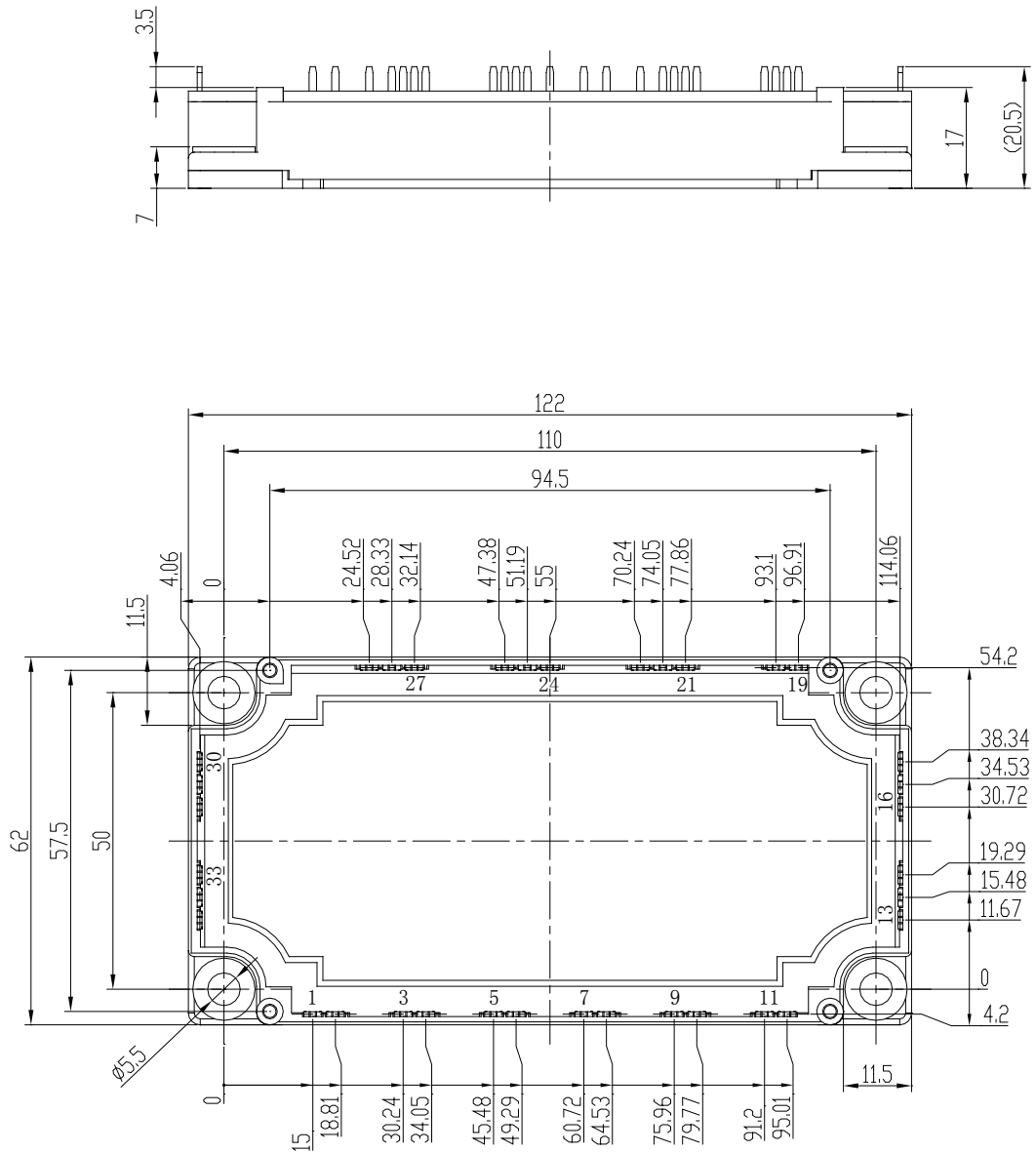
Fig 11. NTC Temperature Characteristic

**Circuit Schematic**



**Package Dimensions**

Dimensions in Millimeters





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